

To: Semiconductor Science and Technology Editorial Board
Subject: Article Submit

Dear Editors,

Enclosed with the letter, you will find the electronic submission of the manuscript entitled “Defect engineering using microwave processing in SiC and GaAs” O. Olikh and P. Lytvyn. It is an original paper that has not been simultaneously submitted as a whole or in part anywhere else. No conflict of interest exists in the submission of this manuscript.

The defects are known to be crucial for the semiconductor structure performance. As a result, the methods intended to modify the system of defects are very important for practical applications. The influence of certain factors, for example, radiation, has been studied quite well. At the same time, new agents begin to attract more attention, such as ultrasound loading or microwave treatment (MWT). The present manuscript describes the effect of MWT on the parameters of deep centers located in the near-surface region of single crystals n -6H-SiC, n -GaAs, and epi-GaAs epitaxial structures. In particular the abruptness of interstitial atoms are revealed. We believe that such a way of defect engineering would be of interest to the readers.

We would very much appreciate it if you would consider the manuscript for publication in the *Semiconductor Science and Technology*.

Sincerely yours,
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